NSN 5962-01-370-1475

Memory Microcircuit - Page 1 of 1



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| Maximum Power Dissipation Rating: |
|---|
| 1.02 watts |
| Operating Tempurature Range: |
| -55.0/+125.0 degrees celsius |
| Storage Tempurature Range: |
| -65.0/+150.0 degrees celsius |
| Features Provided: |
| Bipolar |
| Inclosure Material: |
| Ceramic |
| Inclosure Configuration: |
| Dual-in-line |
| Output Logic Form: |
| Bipolar metal-oxide semiconductor |
| Case Outline Source And Designator: |
| D-9 mil-m-38510 |
| Current Rating Per Characteristic: |
| -30.00 milliamperes collector cutoff current, dc, with specified resistance between base and emitter microamperes and 5.00 milliamperes |
| reverse current, dc microamperes |
| Terminal Surface Treatment: |
| Solder |
| Product Name: |
| Microcircuit, digital, schottky, bipolar 16384 bit prom |
| Voltage Rating And Type Per Characteristic: |
| -0.5 volts total supply and 7.0 volts total supply |
| Time Rating Per Chacteristic: |
| 65.00 nanoseconds access |
| Memory Device Type: |
| Prom |
| Hybrid Technology Type: |
| Monolithic |
| Test Data Document: |
| 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). |
| Terminal Type And Quantity: |
| 24 printed circuit |
| Shelf Life: |
| N/a |
| Unit Of Measure: |
| |
| Demilitarization: |
| Yes - demil/mli |
| Fiig: |

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